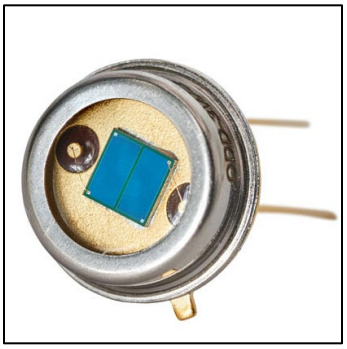
Red Enhanced 3.1 mm² X 2 Bi-Cell Photodiode ODD-3W-2



FEATURES

- Red Enhanced
- Low Noise
- High Response
- High Shunt Resistance
- Low Profile TO-5 Package

Electro-Optical Characteristics at 25°C

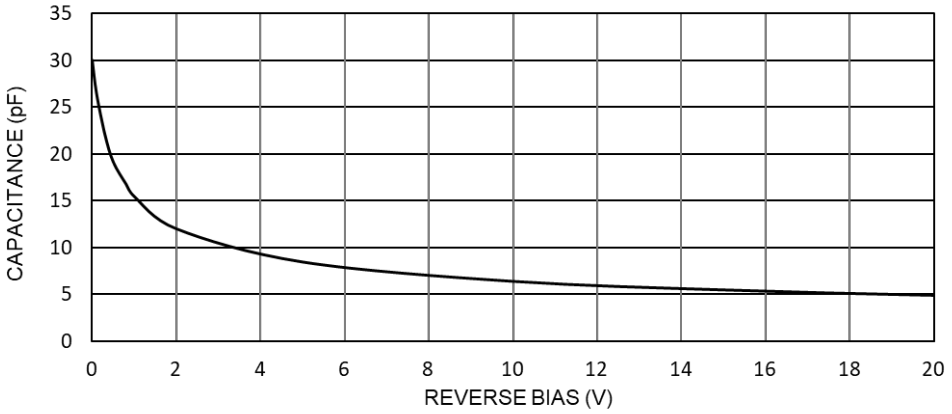
Characteristic	Test Conditions	Min	Typ	Max	Units
Dark Current, I_D	V_R = 5 V		0.9	5	na
Shunt Resistance, R_{SH}	V_R = 10 mV		300		MΩ
Junction Capacitance, C_J	V_R = 0 V, f = 1 MHz		30		pF
Junction Capacitance, C_J	V_R = 10 V, f = 1 MHz		7.5		pF
Spectral Application Range, λrange	Spot Scan	250		1100	nm
Responsivity, R	λ = 633 nm, V_R = 0 V	0.32	0.36		A/W
Responsivity, R	λ = 900 nm, V_R = 0 V	0.5	0.6		A/W
Breakdown Voltage, V_R	I_R = 10 µA	25	60		V
Noise Equivalent Power, NEP	V_R = 0 V, λ = 950 nm		2.5×10^{-14}		W/√HZ
Response Time, t_r[1]	RL = 50 Ω, V_R = 0 V		190		nsec
Response Time, t_r[1]	RL = 50 Ω, V_R = 10 V		8		nsec

[1] Response time of 10% to 90% is specified at 660 nm.

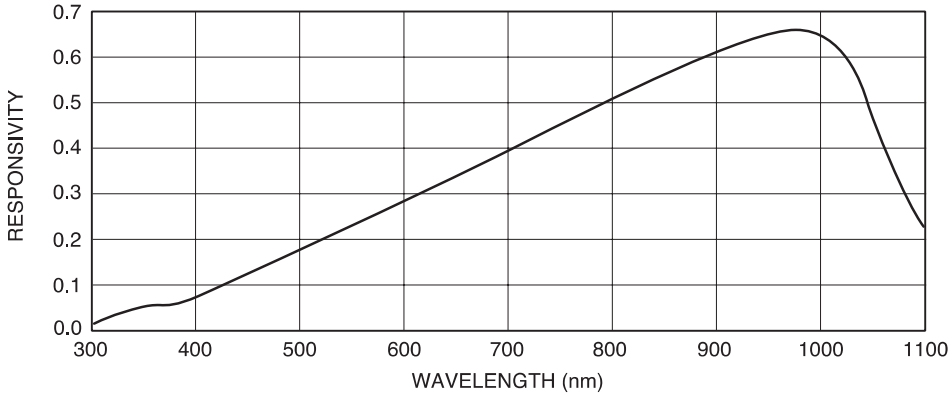
Absolute Maximum Ratings at 25°C

Parameter	Min	Max	Units
Reverse Voltage, V_R		100	V
Storage Temperature, T_{STG}	-55	+150	°C
Operating Temperature, T_O	-40	+125	°C
Lead Soldering Temperature (1/16" from case for 3 sec)		+260	°C

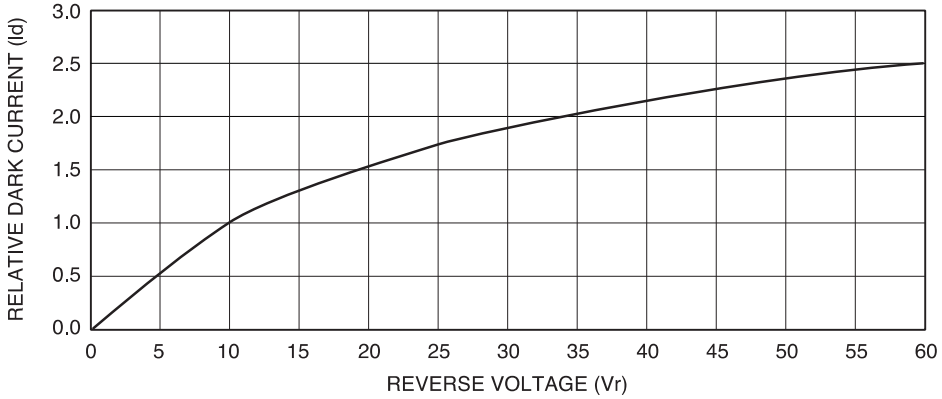
Capacitance vs. Bias Voltage



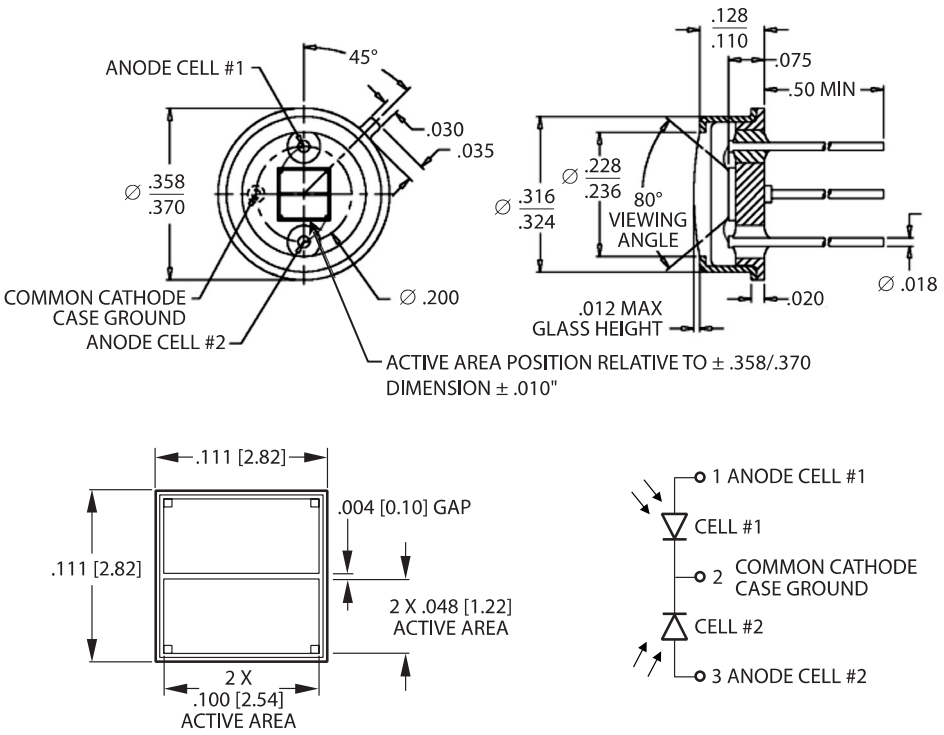
Typical Spectral Response



Dark Current vs Voltage



Package Information



Dimensions are in inch [metric] units.

Specifications are subject to change without prior notice.